

IN THE CLAIMS:

Please rewrite claims 2, 5, 7, 9, 10, 13 - 15, 17, 19, 21, 22, 25 - 28, 30 and 32 as set forth below in clean form below. Additionally, in accordance with 37 CFR § 1.121(c)(1)(ii), amended claims 2, 5, 7, 9, 10, 13 - 15, 17, 19, 21, 22, 25 - 28, 30 and 32 are set forth in a marked-up version in the pages attached hereto as APPENDIX III.

--2. (Twice amended) The method of forming a solid of a ferroelectric or a high dielectric material according to Claim 1, wherein said organic substance removing step includes a depressurizing step of placing said organic compound material in a low-pressure atmosphere.--

--5. (Twice amended) The method of forming a solid of a ferroelectric or a high dielectric material according to Claim 1, wherein said organic substance removing step includes a step of giving energy other than heat to said organic compound materials.--

--7. (Twice amended) The method of forming a solid of a ferroelectric or a high dielectric material according to Claim 5, wherein said step of giving energy other than heat includes a step of treating said organic compound materials with activated oxygen particles.--

--9. (Twice amended) The method of forming a solid of a ferroelectric or a high dielectric material according to Claim 1, wherein said inorganic compound solid is a complex oxide.

10. (Twice amended) A method of manufacturing a semiconductor device, comprising a step of forming, on a semiconductor substrate, a functional thin film made of a solid of a ferroelectric or a high dielectric material formed by the method according to Claim 1.--

--13. (Amended) The method of manufacturing a semiconductor device according to

Claim 11, wherein said treatment step of giving energy other than heat to said functional thin film includes an oxygen activated particle treatment step of placing said semiconductor substrate having formed thereon said functional thin film in an oxygen activated particle atmosphere.--

--14. (Amended) The method of manufacturing a semiconductor device according to Claim 11, wherein said treatment step of giving energy other than heat to said functional thin film includes an electromagnetic wave supplying step of supplying an electromagnetic wave to said functional thin film.

15. (Amended) The method of manufacturing a semiconductor device according to Claim 11, further comprising a wire forming step of forming a wiring on said semiconductor substrate before said restoring step.--

--17. (Amended) The method of manufacturing a semiconductor device according to Claim 11, further comprising an element forming step of forming a functional element on said semiconductor substrate before said restoring step.--

--19. (Amended) The method of manufacturing a semiconductor device according to Claim 10, comprising an element forming step of forming a functional element on said semiconductor substrate before said step of forming said functional thin film.--

--21. (Amended) The method of manufacturing a semiconductor device according to Claim 10, wherein said crystallizing step is carried out at a predetermined temperature lower than a temperature, at or above which mutual-diffusion of materials occurs between said functional thin film and a solid adjacent thereto.

22. (Amended) The method of manufacturing a semiconductor device according to Claim 10, wherein:

said functional thin film is a ferroelectric thin film; and

said semiconductor device is a ferroelectric storage device employing said ferroelectric thin film as a charge holding film.--

--25. (Amended) The method of manufacturing a semiconductor device according to Claim 23, wherein said restoring step further includes an oxygen introducing step of introducing an oxidation gas to a surface of said semiconductor substrate having formed thereon said functional thin film.

26. (Amended) The method of manufacturing a semiconductor device according to Claim 23, wherein said treatment step of giving energy other than heat to said functional thin film includes an oxygen activated particle treatment step of placing said semiconductor substrate having formed thereon said functional thin film in an oxygen activated particle atmosphere.

27. (Amended) The method of manufacturing a semiconductor device according to Claim 23, wherein said treatment step of giving energy other than heat to said functional thin film includes an electromagnetic wave supplying step of supplying an electromagnetic wave to said functional thin film.

28. (Amended) The method of manufacturing a semiconductor device according to Claim 23, further comprising a wiring forming step of forming a wiring on said semiconductor substrate before said restoring step.--

--30. (Amended) The method of manufacturing a semiconductor device according to Claim 23, further comprising an element forming step of forming a functional element on said semiconductor substrate before said restoring step.--

--32. (Amended) The method of manufacturing a semiconductor device according to Claim 23, wherein said functional thin film is a ferroelectric thin film.--

REMARKS

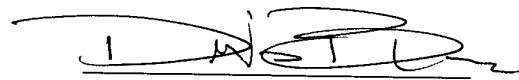
This Preliminary Amendment is requested prior to the initial examination of the above-identified patent application to replace specification and to eliminate multiple

ROH-039

PATENT APPLICATION

dependency. If the Examiner has any suggestions for placing this application in even better form, the Examiner is invited to telephone the undersigned and the number listed below.

Respectfully submitted,



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Date: May 25, 2001

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